EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	"6255180"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 18:22
L2	11425	((257/59) or (257/72) or (257/351) or (257/355) or (257/356) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395) or (257/406)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/28 18:54
L3	33	L2 and gate adj insulat$3.clm. and "high" adj2 voltage.clm. and "low" adj2 voltage.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 18:55
L4	6	((nec).as. (okumura near1 hiroshi).as.) and gate adj insulat$3.clm. and "high" adj2 voltage.clm. and "low" adj2 voltage.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 18:57
L5	0	((nec).as. (okumura near1 hiroshi).as.) and gate adj insulat$3.clm. and "high" adj2 voltage.clm. and "low" adj2 voltage.clm. and (below underneath) near4 (direct directly immediately vertical vertically)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 19:02
S1	2	jp-05335573$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/27 16:09
S2	0	jp-200345892$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S3	2	jp-2003045892$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37

S4	2	jp-08250742$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S5	2	jp-11307777$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:37
S6	2	jp-2000353811$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:41
S7	10	S1 S2 S3 S4 S5 S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 17:11
S8	5	"773333".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 16:44
S9	18	(tft thin adj film adj transistor) and overlap near6 ("low" "high") near2 voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:05
S10	4455	"low" near2 voltage and "high" near2 voltage and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:09
S11	80	"low" near2 voltage near20 gate adj (insulation insulating oxide) and "high" near2 voltage near20 gate adj (insulation insulating oxide) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:10
S12	5683	((257/59) or (257/72) or (257/351) or (257/355) or (257/356) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395) or (257/406)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 17:39

S13	19	S12 and gate adj insulat$3. clm. and "high" adj2 voltage.clm. and "low" adj2 voltage.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/05 17:44
S14	133	(257/406).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 17:44
S15	42	(US-20040195568-$ or US-20040046174-$ or US-20030025127-$ or US-20020149056-$ or US-20020135554-$ or US-20020042170-$ or US-20020041350-$ or US-20020030190-$ or US-20020024048-$ or US-20010013912-$ or US-20010000755-$ or US-20040026750-$ or US-20020084490-$).did. or (US-6856360-$ or US-6657228-$ or US-6452211-$ or US-6426787-$ or US-6420988-$ or US-6400434-$ or US-6384886-$ or US-6368904-$ or US-6316787-$ or US-6303963-$ or US-6294815-$ or US-6165824-$ or US-6163055-$ or US-6115094-$ or US-5528056-$ or US-6597046-$ or US-5468987-$).did. or (JP-2003045892-$ or JP-2000353811-$ or JP-11307777-$ or JP-08250742-$ or JP-05335573-$ or JP-54015678-$ or JP-02222169-$).did. or (US-20030025127-$ or JP-2000353811-$ or JP-11307777-$ or JP-08250742-$ or JP-05335573-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:05
S16	317	(257/391).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 18:06

S17	46	(US-20040195568-$ or US-20040046174-$ or US-20030025127-$ or US-20020149056-$ or US-20020135554-$ or US-20020042170-$ or US-20020041350-$ or US-20020030190-$ or US-20020024048-$ or US-20010013912-$ or US-20010000755-$ or US-20040026750-$ or US-20020084490-$ or US-20020190343-$ or US-20020117723-$).did. or (US-6856360-$ or US-6657228-$ or US-6452211-$ or US-6426787-$ or US-6420988-$ or US-6400434-$ or US-6384886-$ or US-6368904-$ or US-6316787-$ or US-6303963-$ or US-6294815-$ or US-6165824-$ or US-6163055-$ or US-6115094-$ or US-5528056-$ or US-6597046-$ or US-5468987-$ or US-6541823-$ or US-5576556-$).did. or (JP-2003045892-$ or JP-2000353811-$ or JP-11307777-$ or JP-08250742-$ or JP-05335573-$ or JP-54015678-$ or JP-02222169-$).did. or (US-20030025127-$ or JP-2000353811-$ or JP-11307777-$ or JP-08250742-$ or JP-05335573-$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:33
S18	5	S17 and double adj gate	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:35
S19	2	S17 and ((additional extra second double) adj gate sub-gate) near5 (withstand break-down breakdown) near2 voltage	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 18:47
S20	326	(257/392).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 18:57
S21	138	(257/270).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 18:59
S22	264	(257/346).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/05 19:06

S23	159	(257/387).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/08/16 12:38
S24	5	"low" near1 voltage near10 (tft thin adj film adj transistor) near10 (self-alignment selfaligned overlap overlapping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 19:14
S25	82	(US-20040195568-$ or US-20040046174-$ or US-20030025127-$ or US-20020149056-$ or US-20020135554-$ or US-20020042170-$ or US-20020041350-$ or US-20020030190-$ or US-20020024048-$ or US-20010013912-$ or US-20010000755-$ or US-20040026750-$ or US-20020084490-$ or US-20020190343-$ or US-20020117723-$ or US-20030132500-$).did. or (US-6856360-$ or US-6657228-$ or US-6452211-$ or US-6426787-$ or US-6420988-$ or US-6400434-$ or US-6384886-$ or US-6368904-$ or US-6316787-$ or US-6303963-$ or US-6294815-$ or US-6165824-$ or US-6163055-$ or US-6115094-$ or US-5528056-$ or US-6597046-$ or US-5468987-$ or US-6541823-$ or US-5576556-$ or US-6847080-$ or US-6847088-$ or US-6853030-$ or US-6770940-$ or US-6653694-$ or US-6646313-$ or US-6627963-$).did. or (US-6593191-$ or US-6586805-$ or US-6579736-$ or US-6563182-$ or US-6559489-$ or US-6492690-$ or US-6380590-$ or US-6333541-$ or US-6300663-$ or US-6271572-$ or US-6267479-$ or US-6265739-$ or US-6251732-$ or US-6198140-$ or US-6191460-$ or US-6175138-$ or US-6166417-$ or US-6093594-$ or US-5696400-$ or US-5654577-$ or US-4205330-$ or US-4183040-$ or US-4104784-	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/05 19:19

		$ or US-4085498-$ or US-6157062-$ or US-6064096-$ or US-5736750-$).did. or (US-6469348-$).did. or (JP-2003045892-$ or JP-2000353811-$ or JP-11307777-$ or JP-08250742-$ or JP-05335573-$ or JP-54015678-$ or JP-02222169-$).did. or (US-20030025127-$ or JP-2000353811-$ or JP-11307777-$ or JP-08250742-$ or JP-05335573-$).did.				
S26	10	(JP-05335573-$ or JP-08250742-$ or JP-11307777-$ or JP-2000353811-$ or JP-2003045892-$).did. or (JP-05335573-$ or JP-08250742-$ or JP-11307777-$ or JP-2000353811-$ or US-20030025127-$).did.	JPO; DERWENT	OR	OFF	2005/03/05 19:43
S27	1	("6509602").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 19:51
S28	14	S25 and (overlap overlapping) near4 (source drain gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 19:52
S29	1	ikeda.in. and yamazaki.in. and thinner.ab. and gate and pixel and TFT.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 20:16
S30	465	(overlap overlapping) near10 (self-alignment self-aligned) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:34
S31	207	(overlap overlapping) near4 (self-alignment self-aligned) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:34

S32	102	(overlap overlapping) near4 (self-alignment self-aligned) near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:35
S33	22	(overlap overlapping) near4 (self-alignment self-aligned) near4 gate and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/05 21:35
S34	82	(US-20010000755-$ or US-20010013912-$ or US-20020024048-$ or US-20020030190-$ or US-20020041350-$ or US-20020042170-$ or US-20020084490-$ or US-20020117723-$ or US-20020135554-$ or US-20020149056-$ or US-20020190343-$ or US-20030025127-$ or US-20030132500-$ or US-20040026750-$ or US-20040046174-$ or US-20040195568-$).did. or (US-4085498-$ or US-4104784-$ or US-4183040-$ or US-4205330-$ or US-5468987-$ or US-5528056-$ or US-5576556-$ or US-5654577-$ or US-5696400-$ or US-5736750-$ or US-6064096-$ or US-6093594-$ or US-6115094-$ or US-6157062-$ or US-6163055-$ or US-6165824-$ or US-6166417-$ or US-6175138-$ or US-6191460-$ or US-6198140-$ or US-6251732-$ or US-6265739-$ or US-6267479-$ or US-6271572-$ or US-6294815-$ or US-6300663-$).did. or (US-6303963-$ or US-6316787-$ or US-6333541-$ or US-6368904-$ or US-6380590-$ or US-6384886-$ or US-6400434-$ or US-6420988-$ or US-6426787-$ or US-6452211-$ or US-6469348-$ or US-6492690-$ or US-6541823-$ or US-6559489-$ or US-6563182-$ or US-6579736-$ or US-6586805-$ or US-6593191-$ or US-	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/06 07:33

		6597046-$ or US-6627963-$ or US-6646313-$ or US-6653694-$ or US-6657228-$ or US-6770940-$ or US-6847080-$ or US-6847088-$ or US-6853030-$).did. or (US-6856360-$).did. or (JP-02222169-$ or JP-05335573-$ or JP-08250742-$ or JP-11307777-$ or JP-2000353811-$ or JP-2003045892-$ or JP-54015678-$).did. or (JP-05335573-$ or JP-08250742-$ or JP-2000353811-$ or JP-11307777-$ or US-20030025127-$).did.				
S35	3	S34 and yanai.in.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/03/06 07:40
S36	28	(self-aligned self-aligning self-alignment) near10 (". ANG." ".mu.m" micron nm nanometer Angstrom) and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 07:45
S37	22	(self-aligned self-aligning self-alignment) and LDD and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 07:55
S38	15	(self-aligned self-aligning self-alignment) and LDD and "low" near1 voltage and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 07:56
S39	15	(self-aligned self-aligning self-alignment) and LDD and "low" near1 voltage and "high" near1 voltage and S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:05
S40	126	LDD near4 "low" near1 voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:05
S41	14	LDD near4 "low" near1 voltage and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:36

S42	5	LDD near4 "low" near1 voltage and tft and (self-aligned self-aligning self-alignment selfaligned selfaligment)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 08:36
S43	238	second adj electrode near6 TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 10:21
S44	19	split-gate and TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 10:27
S45	131	separate near1 gate and TFT	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/06 12:22
S46	60	separate near1 gate and TFT	US-PGPUB	OR	OFF	2005/03/06 12:25
S47	654	double adj gate and tft	US-PGPUB	OR	OFF	2005/03/06 12:26
S48	15	double adj gate.ti,ab,clm. and tft	US-PGPUB	OR	OFF	2005/03/06 12:48
S49	2	(overlap overlapping) near6 gate near6 (".mu.m" ".ANG." nm nanometer micron) and tft.ti,ab,clm.	US-PGPUB; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:01
S50	7	(overlap overlapping) near6 gate near6 (".mu.m" ".ANG." nm nanometer micron) and tft	US-PGPUB; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:36
S51	83	(overlap overlapping) near6 (".mu.m" ".ANG." nm nanometer micron) and tft	US-PGPUB; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:36
S52	10	(JP-2003045892-$ or JP-2000353811-$ or JP-05335573-$ or JP-11307777-$ or JP-08250742-$).did. or (JP-2000353811-$ or US-20030025127-$ or JP-08250742-$ or JP-11307777-$ or JP-05335573-$).did.	JPO; DERWENT	OR	OFF	2005/03/06 13:50

S53	11	(JP-2003045892-$ or JP-2000353811-$ or JP-05335573-$ or JP-11307777-$ or JP-08250742-$).did. or (JP-2000353811-$ or US-20030025127-$ or JP-08250742-$ or JP-11307777-$ or JP-05335573-$).did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/06 13:52
S54	266	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/03/06 13:52
S55	144	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:52
S56	47	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain and tft.ti,ab,clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:56
S57	7	width near4 gate adj electrode and (overlap overlapping) near6 gate near6 drain near6 ("mu.m" nm ".ANG.") and tft	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/03/06 13:57
S58	2	jp-05335573$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 09:53
S59	2	jp-08250742$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 08:41
S60	0	jp-200345892$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 08:41
S61	2	jp-2003045892$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 08:41
S62	346	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 09:53

S63	325	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:54
S64	41	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:55
S65	7	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 10:19
S66	0	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. and polysilicon adj tft near4 polyslicon near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:56
S67	0	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. and polysilicon adj tft near10 polyslicon near10 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:56
S68	0	gate adj electrode near4 polysilicon.ti,ab,clm. and (tft thin adj film adj transistor).ti,ab,clm. and polysilicon adj tft.ti. and polysilicon adj tft same polyslicon near10 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 09:56
S69	2	jp-2000058849$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 10:22
S70	2	jp-11307777$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 10:28
S71	2	jp-2003017502$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:14

S72	2	"20020195604".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 10:29
S73	8649	((257/59) or (257/72) or (257/270) or (257/346) or (257/351) or (257/355) or (257/356) or (257/387) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 12:40
S74	1420	S73 and (third three) near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 12:40
S75	657	S73 and (third three) near4 gate and (tft otft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 12:41
S76	2	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft) and 257/270.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:16
S77	182	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft)"ti,ab, clm."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:17
S78	8	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft).ti,ab, clm. and (overlap overlaps overlapping overlapped) and (self-aligned self-alignment self-align)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:19
S79	0	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft).ti,ab, clm. and (overlap overlaps overlapping overlapped) and (self-aligned self-alignment self-align) and low-voltage and high-voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:19

S80	6	(gate adj stack gate-stack) and (thin adj film adj transistor tft otft).ti,ab,clm. and (overlap overlaps overlapping overlapped) and (self-aligned self-alignment self-align) and ("low" adj voltage "lower" adj voltage low-voltage and "higher" adj voltage "high" adj voltage high-voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 14:20
S81	2	jp-05335573$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:27
S82	2	("5396084").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:42
S83	127	mondt.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:47
S84	462	(tft otft thin adj film adj transistor).ti,ab,clm. and (self-align$2 self-alignment selfalign$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:58
S85	440	(tft otft thin adj film adj transistor).ti,ab,clm. and (self-align$2 self-alignment selfalign$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) and (thick thickness thicker)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:59

S86	307	(tft otft thin adj film adj transistor).ti,ab,clm. and (self-align$2 self-alignment selfalign$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) and (thick thickness thicker) near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 14:59
S87	278	(tft otft thin adj film adj transistor).ti,ab,clm. and (self-align$2 self-alignment selfalign$2 selfalignment) and ((voltage near4 ("high" "higher")) high-voltage) and ((voltage near4 ("low" "lower")) low-voltage) and (thick thickness thicker) near6 gate near6 (insulation insulating oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 15:00
S88	0	(additional second third separate) near4 gate.clm. and (low-voltage (("lower" "low") near2 voltage)).clm. and (high-voltage (("higher" "high") near2 voltage)).clm. and (thin adj film near2 transistor tft otft).clm. and (overlap overlapped overlaps overlapping).clm. and (self-align self-alignment self-aligned self-aligning).clm. and (thick thickness thicker).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 16:36
S89	2	jp-2000058849$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 17:10
S90	2	jp-11307777$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 17:08
S91	2	jp-2003017502$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 16:37

S92	2	"20020195604".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 17:10
S93	8	S89 S90 S91 S92	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/16 16:37
S94	2	("20030025127").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/16 16:59
S95	2	jp-2003017502$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/17 11:56
S96	5	"773333".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/17 12:18
S97	1	(low-voltage "low" adj voltage) and (tft thin adj film adj transistor) and (self-align$3 self-aligned self-alignment selfalign$3 selfalignment) and overlap near4 (".mu.m" micron ">ANG." Angstrom Angstroem)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 12:20
S98	1	(low-voltage "low" adj voltage) and (tft thin adj film adj transistor) and (self-align$3 self-aligned self-alignment selfalign$3 selfalignment) and overlap near4 (".mu.m" micron "ANG." Angstrom Angstroem)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 12:21
S99	1	(low-voltage "low" adj voltage) and (tft thin adj film adj transistor) and (self-align$3 self-aligned self-alignment selfalign$3 selfalignment) and (overlapping overlapped overlap) near4 (".mu.m" micron "ANG." Angstrom Angstroem)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 12:22

S100	14	(tft thin adj film adj transistor) and (self-align $3 self-aligned self-alignment selfalign$3 selfalignment) and (overlapping overlapped overlap) near4 (".mu.m" micron "ANG." Angstrom Angstroem)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 12:59
S101	2219	(self-alignment self-align$3 selfalign$3 selfalignment).ti,ab,clm. and (LDD lightly adj doped adj drain lightly-doped adj dran)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:00
S102	2219	(self-alignment self-align$3 selfalign$3 selfalignment).ti,ab,clm. and (LDD lightly adj doped adj drain lightly-doped adj drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:00
S103	1012	(self-alignment self-align$3 selfalign$3 selfalignment).ti,ab,clm. and (LDD lightly adj doped adj drain lightly-doped adj drain).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:00
S104	136	(self-alignment self-align$3 selfalign$3 selfalignment).ti,ab,clm. and (LDD lightly adj doped adj drain lightly-doped adj drain).ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:05
S105	5	(self-alignment self-align$3 selfalign$3 selfalignment).ti,ab,clm. and (LDD lightly adj doped adj drain lightly-doped adj drain).ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab,clm. and hot adj electron adj effect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:05
S106	9	(self-alignment self-align$3 selfalign$3 selfalignment).ti,ab,clm. and (LDD lightly adj doped adj drain lightly-doped adj drain).ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab,clm. and hot adj electron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/17 13:05

S107	9207	((257/72) or (257/59) or (257/270) or (257/346) or (257/351) or (257/387) or (257/355) or (257/356) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395) or (257/406)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/18 15:49
S108	3	S107 and (thin adj film adj transistor tft otft) and (high $3 near1 voltage) and (low $3 near1 voltage) and gate near2 (silicide near3 (silicon semiconductor)) and overlap$4 near6 (source drain gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/01 11:27
S109	2	JP-2000193774$-$.DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/01 12:26
S110	11789	257/72 257/59 257/270 257/346 257/351 257/387 257/355 257/356 257/390 257/391 257/392 257/393 257/394 257/395 257/406	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/18 15:50
S111	6806	((self-align$4 selfalign$4) gate near3 (drain source) near3 overlap) and (thin adj film adj transistor tft otft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 15:53
S112	1213	((self-align$4 selfalign$4) (gate near3 (drain source) near3 overlap)).ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:10
S113	18	((self-align$4 selfalign$4) (gate near3 (drain source) near3 overlap)).ti,ab,clm. and (thin adj film adj transistor tft otft).ti,ab, clm. and third adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:29
S114	0	(thickness thick) near6 gate adj electrode and "773333".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:30
S115	1	(thickness thick) near6 (gate adj electrode) and "773333".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:37

S116	1	(thickness thick) near6 (gate adj electrode) and "773333".ap. and (thick thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:46
S117	1	overlap$4 near4 (second adj gate) and "773333". ap. and (thick thickness)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:48
S118	1	overlap$4 near4 (second adj gate) and "773333". ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:49
S119	0	overlap$4 near10 ".mu.m" and "773333".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:49
S120	1	overlap$4 and "773333". ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:06
S121	0	".mu.m" and "773333".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 16:50
S122	296	(overlap$4 near4 gate).ti, ab,clm. and S112	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 17:10
S123	257	(overlap$4 near4 gate).ti, ab,clm. and S112 and @ad<"20040210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:17
S124	218	(overlap$4 near4 gate near4 (source drain)).ti,ab, clm. and S112 and @ad<"20040210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:18
S125	0	(overlap$4 near4 gate near4 (source drain) near4 nm).ti,ab,clm. and S112 and @ad<"20040210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:18

S126	1	(overlap$4 near4 gate near4 (source drain) near4 micron).ti,ab,clm. and S112 and @ad<"20040210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:22
S127	5	(overlap$4 near4 gate near4 (source drain) near4 micron).ti,ab,clm. and @ad<"20040210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/18 18:22
S128	10	(JP-2003045892-$ or JP-2000353811-$ or JP-11307777-$ or JP-08250742-$ or JP-05335573-$).did. or (JP-11307777-$ or JP-08250742-$ or JP-05335573-$ or US-20030025127-$ or JP-2000353811-$).did.	JPO; DERWENT	OR	OFF	2006/09/18 19:16
S129	4	S128 and (thick thickness) near4 gate	JPO; DERWENT	OR	ON	2006/09/18 19:16
S130	93	(US-20040195568-$ or US-20010000755-$ or US-20010013912-$ or US-20020030190-$ or US-20020041350-$ or US-20020042170-$ or US-20020135554-$ or US-20020149056-$ or US-20030025127-$ or US-20040048422-$ or US-20020024048-$ or US-20040206956-$ or US-20040046174-$ or US-20020195604-$ or US-20030132500-$ or US-20050167668-$ or US-20040257486-$ or US-20020117723-$ or US-20040012023-$ or US-20020190343-$ or US-20020139978-$ or US-20030124778-$ or US-20040026750-$ or US-20020084490-$).did. or (US-6627963-$ or US-6856360-$ or US-5736750-$ or US-6657228-$ or US-4085498-$ or US-6271572-$ or US-6563182-$ or US-6559489-$ or US-6157062-$ or US-4183040-$ or US-6853030-$ or US-5654577-$ or US-6847088-$ or US-	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2006/09/18 19:18

		6541823-$ or US-5468987-$ or US-6064096-$ or US-6333541-$ or US-6653694-$ or US-6166417-$ or US-5576556-$ or US-6191460-$ or US-6251732-$ or US-6300663-$ or US-6593191-$ or US-6198140-$ or US-6586805-$).did. or (US-6175138-$ or US-6384886-$ or US-5696400-$ or US-6452211-$ or US-6426787-$ or US-6294815-$ or US-6316787-$ or US-6115094-$ or US-6368904-$ or US-6420988-$ or US-6646313-$ or US-6770940-$ or US-6163055-$ or US-6469348-$ or US-6093594-$ or US-6380590-$ or US-6267479-$ or US-6579736-$ or US-6492690-$ or US-6847080-$ or US-6597046-$ or US-5528056-$ or US-6400434-$ or US-6303963-$ or US-6165824-$ or US-4104784-$ or US-4205330-$).did. or (US-6265739-$ or US-5508216-$).did. or (JP-2003045892-$ or JP-2000353811-$ or JP-11307777-$ or JP-08250742-$ or JP-05335573-$ or JP-2000058849-$ or JP-54015678-$ or JP-02222169-$ or JP-2003017502-$).did. or (JP-11307777-$ or JP-08250742-$ or JP-05335573-$ or US-20030025127-$ or JP-2000353811-$).did.				
S131	15	S130 and (thick thickness) near4 gates near4 ("same" equal)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2006/09/18 19:21
S132	415	(thick thickness) near4 "gates" near4 ("same" equal) and (thin adj film adj transistor tft)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2006/09/18 19:22
S133	113	(thick thickness) near4 "gates" near4 ("same" equal).ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2006/09/18 19:28

S134	2	JP-2003017502$-$.did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2006/09/18 19:28
S135	15	gate near4 (source drain) near4 overlap$4 near4 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 08:38
S136	68	gate near4 (source drain) near4 overlap$4 near4 "mu.m"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 08:41
S137	21	gate near4 (source drain) near4 overlap$4 near4 "mu.m" and (self-alignment self-aligned self-align)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 08:41
S138	11	("high" adj voltage near2 TFT) and ("low" adj voltage adj TFT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 09:48
S139	54	("high" adj voltage near2 TFT) and ("low" adj voltage near2 TFT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:03
S140	2	"20030025127".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:12
S141	2	"20030025127".pn. and (gate electrode polysilicon W)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:23
S142	1	"20030025127".pn. and (overlap "24" LDD)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:23
S143	1	"20030025127".pn. and (overlap$4 "24" LDD)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:54
S144	2	"5053849".pn. and (overlap $4 "24" LDD)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:54

S145	2	"5053849".pn. and (W polysilicon gate electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:57
S146	0	TFT.ti,ab,clm. and ("low" adj voltage) same (W with polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:59
S147	0	(TFT thin adj film adj transistor).ti,ab,clm. and ("low" adj voltage) same (W with polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:59
S148	0	(TFT thin adj film adj transistor) and gate same ("low" adj voltage) same (W with polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:59
S149	0	(TFT thin adj film adj transistor) and gate same ("low" adj voltage) same (W near20 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:00
S150	58	(TFT thin adj film adj transistor) and gate with (W near6 polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:18
S151	24	(TFT thin adj film adj transistor) and gate with (W near6 polysilicon) and (self-align$4 self adj align $4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:46
S152	2	jp-05335573$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:00
S153	2511	(LDD lightly adj doped) near20 self-align$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:00
S154	1398	(LDD lightly adj doped) near4 self-align$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:01

S155	924	(LDD) near4 self-align$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:01
S156	300	(LDD) near4 self-align$4 and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:01
S157	41	(LDD) near4 self-align$4.ti, ab,clm. and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:37
S158	9829	((257/59) or (257/72) or (257/270) or (257/346) or (257/351) or (257/387) or (257/355) or (257/356) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395) or (257/406)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 13:38
S159	260	S158 and ("low"$3 near20 "high"$3 near20 voltage) and overlap$4 near10 gate near10 (impurity source drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:40
S160	152	S158 and ("low"$3 near20 "high"$3 near20 voltage) and overlap$4 near10 gate near10 (impurity source drain) and @ad<"20020210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:50
S161	341	(hiroshi near2 okumura).in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:51
S162	127	((hiroshi near2 okumura).in. nec.as.) and (tft thin adj film adj transistor).ti, ab,clm. and (overlap$4 self-align$4 self adj align $4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 13:53
S163	2	((hiroshi near2 okumura).in. nec.as.) and (tft thin adj film adj transistor).ti, ab,clm. and (overlap$4 self-align$4 self adj align $4).clm. and gate adj (oxide insulati$2) near4 (thick thickness).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:09

S164	2	jp-06244209$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:09
S165	4	(("20030025127") or ("20030017502")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/07 14:00
S166	2	jp-2003017502$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/07 14:05
S167	7261	"high" near2 voltage and "low" near2 voltage and (tft thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 14:06
S168	289	"high" near2 voltage and "low" near2 voltage and (tft thin adj film adj transistor) and second adj3 transistor and third adj3 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/07 14:07
S169	2	("20040206956").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/08 08:17
S170	1	S169 and overlap$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/08 10:56
S171	7	"380721".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/08 13:07
S173	2	("20040206956").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/08 13:15
S174	0	S173 and "Fig. 18"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/08 13:15

S175	1	S173 and "18"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/08 13:35
S176	2	("4692302").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/08 14:38
S177	1	"20040206956".pn. and overlap$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/08 17:31
S178	0	"20040206956".pn. and overlap$4 near10 voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/08 17:31
S179	0	"20040206956".pn. and overlap$4 near10 (high-voltage low-voltage voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/08 17:32
S180	0	"20040206956".pn. and overlap$4 near20 (high-voltage low-voltage voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/08 17:33
S181	0	"20040206956".pn. and overlap$4 near20 ("141" high-voltage low-voltage voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/08 17:33
S182	0	"20040206956".pn. and overlap$4 near20 ("14"$1 high-voltage low-voltage voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/08 17:33
S183	2	"20040206956".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/08 17:33
S184	1	(US-20040195568-$).did.	US-PGPUB	OR	OFF	2007/03/09 11:53
S185	1	(US-20040195568-$).did. and (thick thickness)	US-PGPUB	OR	ON	2007/03/09 11:53

S186	98	(US-20040206956-$ or US-20040195568-$ or US-20040048422-$ or US-20040046174-$ or US-20030025127-$ or US-20020149056-$ or US-20020135554-$ or US-20020030190-$ or US-20020024048-$ or US-20010013912-$ or US-20020042170-$ or US-20020041350-$ or US-20010000755-$ or US-20040026750-$ or US-20020084490-$ or US-20030132500-$ or US-20020117723-$ or US-20030124778-$ or US-20020139978-$ or US-20020190343-$ or US-20040257486-$ or US-20020175376-$ or US-20040012023-$ or US-20020195604-$ or US-20050167668-$).did. or (US-6657228-$ or US-6856360-$ or US-6452211-$ or US-6426787-$ or US-6420988-$ or US-6400434-$ or US-6384886-$ or US-6368904-$ or US-6316787-$ or US-6303963-$ or US-6294815-$ or US-6165824-$ or US-6163055-$ or US-6115094-$ or US-5528056-$ or US-5696400-$ or US-6646313-$ or US-6300663-$ or US-6198140-$ or US-6597046-$ or US-5468987-$ or US-6847080-$ or US-6770940-$ or US-6847088-$ or US-6627963-$ or US-6541823-$).did. or (US-6191460-$ or US-6175138-$ or US-6333541-$ or US-6251732-$ or US-5508216-$ or US-5576556-$ or US-6853030-$ or US-6593191-$ or US-6579736-$ or US-6559489-$ or US-6492690-$ or US-6653694-$ or US-6586805-$ or US-6563182-$ or US-6271572-$ or US-6265739-$ or US-6166417-$ or US-6380590-$ or US-6267479-$ or US-6093594-$ or US-5736750-$ or US-	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2007/03/09 12:05

		5654577-$ or US-4183040-$ or US-4104784-$ or US-4085498-$ or US-4205330-$ or US-6157062-$).did. or (US-6064096-$ or US-6469348-$ or US-5672888-$ or US-7038283-$).did. or (JP-2003045892-$ or JP-2000353811-$ or JP-11307777-$ or JP-08250742-$ or JP-05335573-$ or JP-02222169-$ or JP-54015678-$ or JP-2000058849-$ or JP-2003017502-$ or JP-06244209-$).did. or (US-20030025127-$ or JP-2000353811-$ or JP-08250742-$ or JP-11307777-$ or JP-05335573-$ or JP-2004253596-$).did.				
S187	3	S186 and nakamura.in.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2007/03/09 15:13
S188	135	gate adj array and gate adj electrode near4 (thickness thick)	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2007/03/09 15:14
S189	16	gate adj array and gate adj electrode near4 (thickness thick) near4 ("same" equal)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/03/09 15:15
S190	0	gate adj array and gate adj electrode near4 (thickness thick) near4 ("same" equal) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/03/09 15:15
S191	164	gate adj electrode near4 (thickness thick) near4 ("same" equal) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/03/09 15:16
S192	88	gate adj electrode near2 (thickness thick) near2 ("same" equal) and (tft thin adj film adj transistor)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/03/09 15:44
S193	88	gate adj electrode near2 (thickness thick) near2 ("same" equal) and (tft thin adj film adj transistor) and (polysilicon gate)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/03/09 17:05

S194	14	third adj gate.ti,ab,clm. and (thin adj film adj transistor tft).ti,ab,clm. and (nec.as. (hiroshi near1 okumura).in.)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/03/09 17:08
S195	11542	((257/59) or (257/72) or (257/270) or (257/346) or (257/351) or (257/387) or (257/355) or (257/256) or (257/39$1) or (257/406)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/09 17:09
S196	40	S195 and third adj gate.clm. and thin adj film adj transistor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/09 17:09
S197	42	S195 and third adj gate.clm. and thin adj film adj transistor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/09 17:09
S198	2	jp-2003017502$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/27 09:48
S199	1710	switched adj terminal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/27 16:09
S200	116	high adj voltage near1 transistor and low adj voltage near1 transistor and third adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/15 20:09
S201	48	high adj voltage near1 transistor and low adj voltage near1 transistor and third adj gate and @ad<"20030221"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/15 20:16
S202	18	(adjust adjusted adjustment adjusting) near3 (height distance) near3 voltage same gate and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/15 20:18
S203	381	(257/250).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/15 21:31

S204	381	S203	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/15 20:40
S205	1	(US-20040195568-$).did.	US-PGPUB	OR	OFF	2007/09/15 21:03
S206	0	(US-20040195568-$).did. and gate near3 length	US-PGPUB	OR	ON	2007/09/15 21:03
S207	1	(US-20040195568-$).did. and gate same length	US-PGPUB	OR	ON	2007/09/15 21:03
S208	1	(US-20040195568-$).did. and gate near10 length	US-PGPUB	OR	ON	2007/09/15 21:03
S209	330	S203 and @ad<"20030221"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 00:04
S210	11232	((257/59) or (257/72) or (257/250) or (257/270) or (257/346) or (257/346) or (257/351) or (257/387) or (257/355) or (257/356) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395) or (257/406)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/16 00:05
S211	50	S210 and ("high"$3 near1 voltage high-voltage) and ("low"$3 near1 voltage low-voltage) and (sub-gate subgate "sub" adj gate auxiliary adj gate third adj gate additional adj gate) and (lightly adj doped adj drain LDD)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/16 00:09
S212	0	((okumura near1 hiroshi).in. nec.as.) and ("high"$3 near1 voltage high-voltage).clm. and ("low"$3 near1 voltage low-voltage).clm. and (sub-gate subgate "sub" adj gate auxiliary adj gate third adj gate additional adj gate).clm. and (lightly adj doped adj drain LDD).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/16 00:10
S213	1	(US-20040195568-$).did.	US-PGPUB	OR	ON	2008/01/07 06:59
S214	1	(US-20040195568-$).did.	US-PGPUB	OR	ON	2008/03/16 14:27

S215	0	(US-20040195568-$).did. and impurity adj region near6 second near6 third	US-PGPUB	OR	ON	2008/03/16 14:57
S216	0	jp-2003017502$-$.did.	US-PGPUB	OR	ON	2008/03/16 15:07
S217	2	jp-2003017502$-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/16 15:07
S218	11764	((257/59) or (257/72) or (257/250) or (257/270) or (257/346) or (257/351) or (257/387) or (257/355) or (257/356) or (257/390) or (257/391) or (257/392) or (257/393) or (257/394) or (257/395) or (257/406)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/16 18:45
S219	5	S218 and (tft otft thin adj film adj transistor) and (self $1alignment self$1align self $1aligning self$1aligned) and ("low" "lower") near2 (voltage potential) and ("high" "higher") near2 (voltage potential) and third adj gate near10 ("between" "amidst" sandwich$3) near10 (LDD lightly adj doped impurity diffusion)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/16 18:49
S220	0	((okumura near1 hiroshi).in. (nec).as.) and (tft otft thin adj film adj transistor) and (self$1alignment self $1align self$1aligning self $1aligned) and ("low" "lower") near2 (voltage potential) and ("high" "higher") near2 (voltage potential) and third adj gate near10 ("between" "amidst" sandwich$3) near10 (LDD lightly adj doped impurity diffusion)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/16 18:51
S221	4	("2003017502").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/18 11:53

S222	11	(LDD lightly-doped adj (drain diffusion)) near6 directly near6 "below" near6 gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 12:11
S223	7	(LDD lightly-doped adj (drain diffusion)) near6 directly near6 "below" near6 gate and @ad<"20040210"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 12:14
S224	13	short adj channel adj effects and high-voltage and thin adj film adj transistor and (LDD lightly-doped adj drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 12:21
S225	690	short adj channel adj effects near20 (LDD lightly-doped adj drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 12:25
S226	404	short adj channel adj effects near6 (LDD lightly-doped adj drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 12:26
S227	213	short adj channel adj effects near6 (LDD lightly-doped adj drain) and (LDD lightly-doped adj drain) near6 gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 12:26
S228	140	short adj channel adj effects near6 (LDD lightly-doped adj drain) and (LDD lightly-doped adj drain) near6 gate and @ad<"20040210"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 12:27
S229	13299	((257/59) or (257/72) or (257/250) or (257/270) or (257/346) or (257/351) or (257/387) or (257/355) or (257/356) or (257/39$1) or (257/406)).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/08/18 13:28

S230	5	S229 and high adj voltage near1 transistor and low adj voltage near1 transistor and third adj gate and (impurity drain LDD lightly-doped adj drain) near6 "below"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 13:30
S231	1	S229 and high adj voltage near1 transistor and low adj voltage near1 transistor.clm. and third adj gate.clm. and (impurity drain LDD lightly-doped adj drain) near6 (overlap $4 "below"".")"clm."	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 13:31
S232	0	(okumura.in. nec.as.) and high adj voltage near1 transistor.clm. and low adj voltage near1 transistor. clm. and third adj gate. clm. and (impurity drain LDD lightly-doped adj drain) near6 (overlap$4 "below").clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 13:32
S233	2	"6104772".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 15:49
S234	2	"20040099175"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 15:53
S235	0	wo0206720$-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 16:09
S236	0	wo200206720$-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 16:09
S237	0	wo-200206720$-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 16:09

S238	10	wo-0206720$-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 16:09
S239	0	wo-02006720$-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 16:09
S240	10	wo-0206720$-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/18 16:09
S241	2	"5940464".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/08/19 15:15
S242	4	("2003017502").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/28 15:00
S243	2	JP-2003017502$-$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 15:01
S244	33672	H01L021/336.ipc.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 15:11
S245	469	S244 and third adj gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 15:12

S246	46	S244 and third adj gate and high$1voltage	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 15:12
S247	17	S244 and third adj gate and high$1voltage and @ad<"20030221"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 15:13
S248	52	S244 and high$1voltage near4 (TFT OTFT MOSFET MISFET transistor) near4 low$1voltage and @ad<"20030221"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 15:19
S249	7	S244 and high$1voltage near4 (TFT OTFT MOSFET MISFET transistor) and lower near4 upper near4 gate and @ad<"20030221"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/28 16:02

2/28/2009 7:02:30 PM
C:\Documents and Settings\jmondt\My Documents\EAST\Workspaces\10773333.wsp